

2N7002W N-Channel MOSFET

General description

N-Channel MOSFET

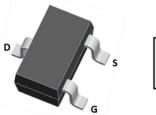
FEATURES

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage

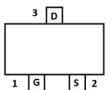
FEATURES

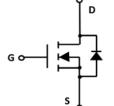
- Battery operated systems
- Solid-state relays
- Direct logic-level interface : TTL/CMOS

V(BR)DSS	RDS(ON)MAX	ID
60V	2.5Ω@10V 340m/	
	3Ω@4.5V	340IIIA



SOT-323





Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

Para	nmeter	Symbol	Limit	Unit	
Drain-source Voltage		V _{DS}	60	V	
Gate-source Voltage		V _{GS}	±30	V	
Peak Gate-source Voltage	Tp<50uS, duty cycle=0.25	V _{GSM}	±40	V	
Drain Current	T _A =25°C @ Steady State	1	340	mΛ	
	T _A =70°C @ Steady State	- I _D	272	mA mA	
Pulsed Drain Current ^A		IDM	1.5	Α	
Total Power Dissipation @ T _A =25℃		P _D	350	mW	
Thermal Resistance Junction-to-Ambient @ Steady State ^B		$R_{ heta JA}$	357	°C/ W	
Junction and Storage Temperature Range		T _J ,T _{STG}	-55∼+150	°C	

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Electrical Characteristics (Ratings at 25° c ambient temperature unless otherwise specified).

Parameter	Symbol	Conditions	Min	Тур	Max	Units	
Static Parameter							
Drain-Source Breakdown Voltage	B _{VDSS}	V _{GS} = 0V, I _D =250μA	60			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V			1	μA	
Gate-Body Leakage Current	I _{GSS1}	V_{GS} = ± 30 V, V_{DS} =0V			±100	nA	
	I _{GSS2}	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±50	nA	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1.0	1.6	2.5	V	
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D =300mA		1.2	2.5	Ω	
		V _{GS} = 4.5V, I _D =200mA		1.3	3.0		
Diode Forward Voltage	V _{SD}	I _S =300mA,V _{GS} =0V			1.2	V	
Maximum Body-Diode Continuous Current	Is				340	mA	
Dynamic Parameters			•				
Input Capacitance	C _{iss}			15			
Output Capacitance	Coss	V _{DS} =30V,V _{GS} =0V,f=1MHZ		9.5		pF	
Reverse Transfer Capacitance	C _{rss}			5.5		1	
Switching Parameters							
Total Gate Charge	Qg	V _{GS} =15V,V _{DS} =30V,I _D =0.3A		1.7	2.4	nC	
Turn-on Delay Time	t _D (on)	V _{GS} =10V,V _{DD} =30V, I _D =300mA,		5		ns	
Turn-off Delay Time	t _D (off)	R_{GEN} =6 Ω		17			
Reverse recovery Time	trr	V_{GS} =0V, I_{S} =300mA, V_{R} =25V, d I_{S} /dt=-100A/ μ s		30		ns	

A. Pulse Test: Pulse Width≤300us, Duty cycle ≤2%.

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B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



Typical characteristics

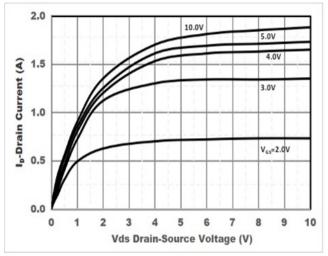


Figure 1. Output Characteristics

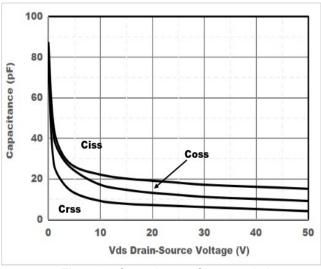


Figure 3. Capacitance Characteristics

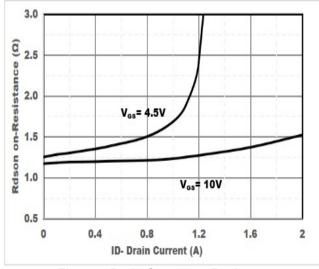


Figure 5. Drain-Source on Resistance

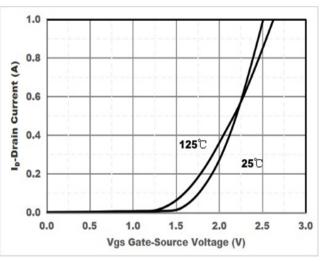


Figure 2. Transfer Characteristics

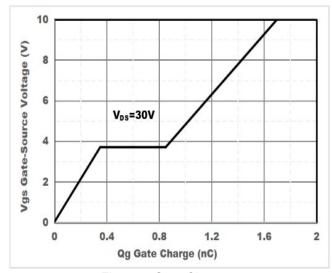


Figure4. Gate Charge

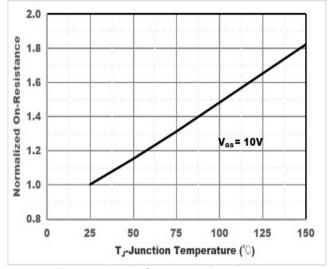


Figure6. Drain-Source on Resistance

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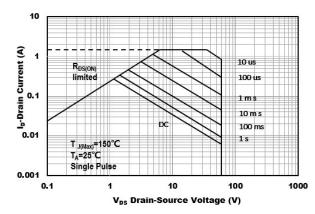


Figure 7. Safe Operation Area

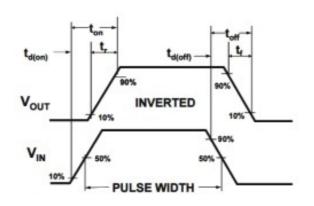
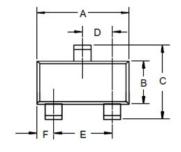
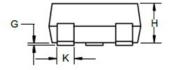
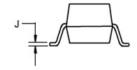


Figure8. Switching wave

SOT-323 Package information

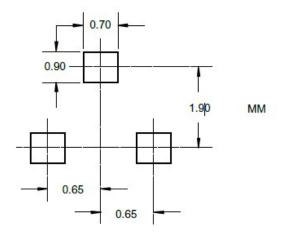






		DIMEN	ISIONS		
DIM	INC	INCHES		MM	
	MIN	MAX	MIN	MAX	NOTE
Α	.071	.087	1.80	2.20	1011/12/12/12
В	.045	.053	1.15	1.35	
С	.083	.096	2.10	2.45	
D	.026 N	lominal	0.65Nom	inal	
E	.047	.055	1.20	1.40	
F	.012	.016	.30	.40	
G	.000	.004	.000	.100	
Н	.035	.039	.90	1.00	
J	.004	.010	.100	.250	
K	.006	.016	.15	.40	

Suggested Pad Layout



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EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 NTE2969 NTE6400A DMC2700UDMQ-7
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